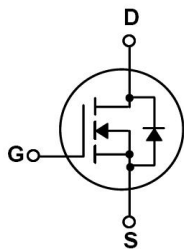
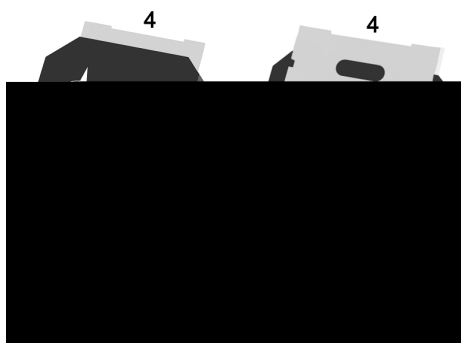


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TO-252 N
 N-CHANNEL MOSFET in a TO-252 Plastic Package.

$V_{DS}=60V$ $I_D=78A$
 $R_{DS(on)}@10V \leq 7m\Omega$ (Type. $5.7m\Omega$)
 $R_{DS(on)}@6V \leq 12m\Omega$ (Type. $6.2m\Omega$)
 HF Product.

GF2GF $\approx \downarrow$
 DC/DC Converter, Ideal for high-frequency switching and synchronous rectification.



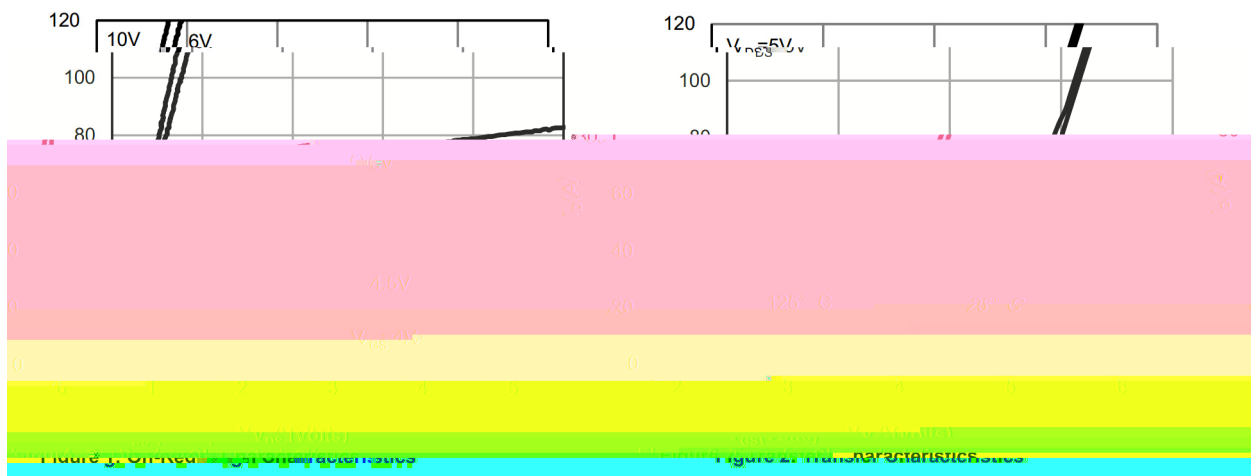
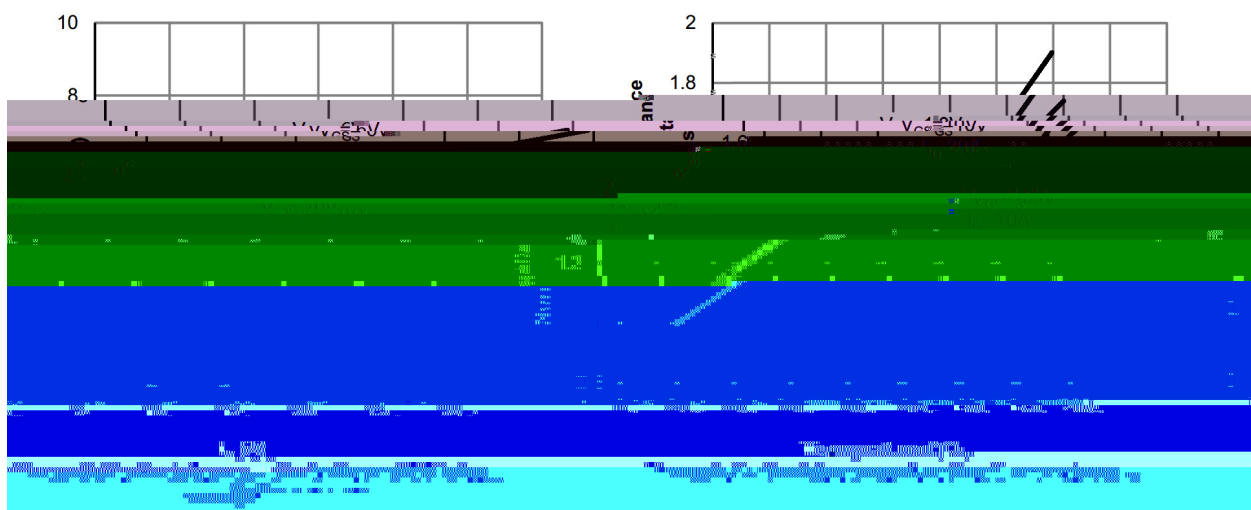
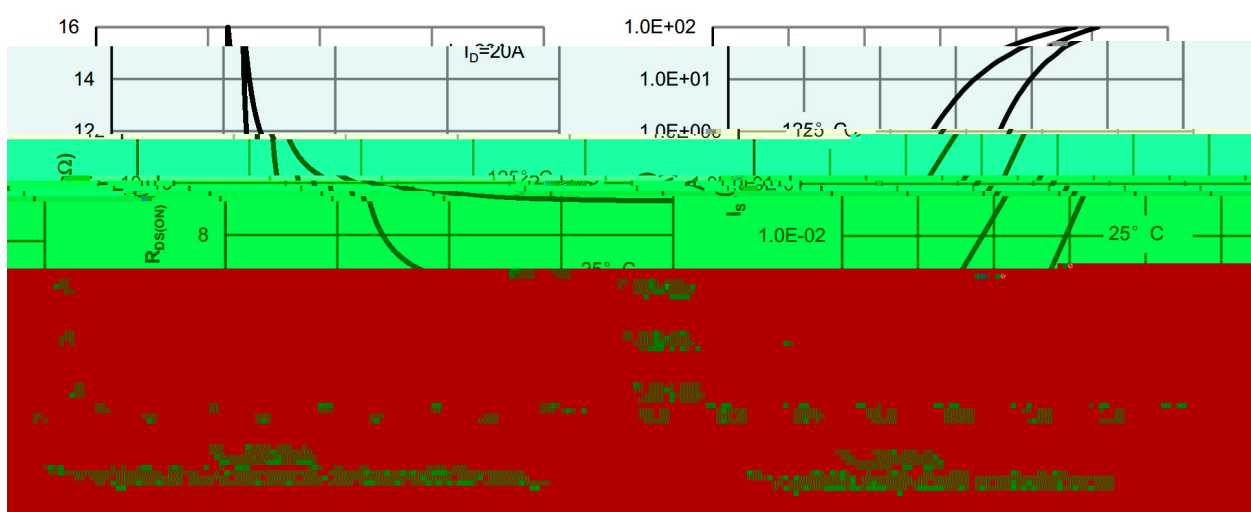
PIN1 G PIN 2 D PIN 3 S PIN 4 D

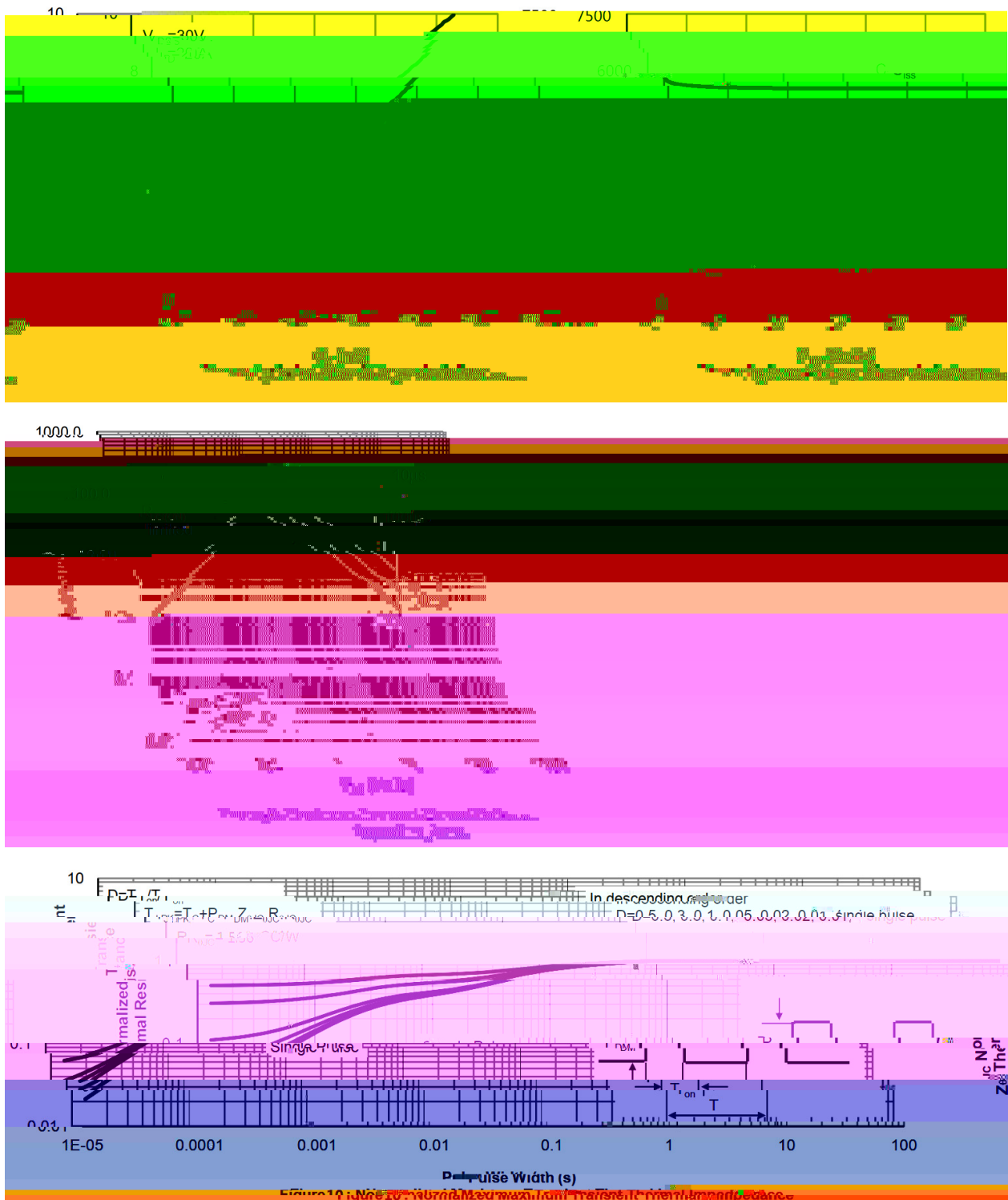
See Marking Instructions.

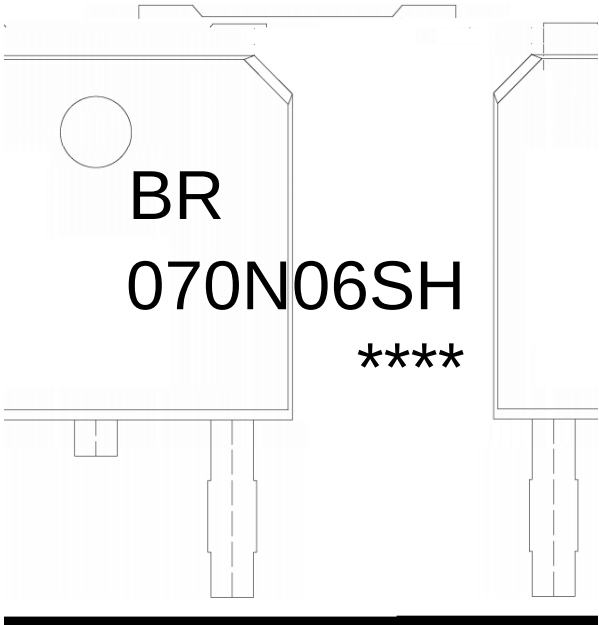
Parameter		N Symbol	Rating	Unit
Drain-Source Voltage		V_{DS}	60	V
Drain Current		$I_D(T_C=25^{\circ}N)$	78	A
Pulsed Drain Current		I_{DM}	274	A
Gate-Source Voltage		V_{GS}	≤ 20	V
Single Pulsed Avalanche Energy(L=0.5mH)		E_{AS}	720	mJ
Avalanche Current		I_{AS}	41	A
Total Power Dissipation		$P_D(T_C=25^{\circ}N)$	150	W
Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 150	
Thermal Resistance-Junction to Ambient	Steady-State	$R_{\theta JA}$	62.5	/W
Thermal Resistance-Junction to Case	Steady-State	$R_{\theta JC}$	1.56	

Parameter	N Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DS}	$I_D=250\mu A, V_{GS}=0V$	60	70		V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=60V, V_{GS}=0V$			1.0	μA
Gate-Body leakage current	I_{GSS}	$V_{DS}=0V, V_{GS}= \pm 20V$			± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	2.0	2.9	4.0	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=20A$		5.7	7	

Parameter	N Symbol	Test Conditions	Min	Typ	Max	Unit
Turn-On Delay Time	$t_{d(on)}$	$V_{GS}=10V$ $V_{DS}=30V$ $R_L=1.5\ \Omega$ $R_{GEN}=3\ \Omega$		21		ns
Turn-On Rise Time	t_r			23		
Turn-Off Delay Time	$t_{d(off)}$			35		
Turn-Off Fall Time	t_f			4.2		







BR	N
070N06SH	N
****	N

Note:

BR:	Company Code
070N06SH:	Product Type Code
****:	Lot No. Code, code change with Lot No

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